**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

### 2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions  | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |   | -   | -   | 600 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ;<br>$t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5      | -   | -   | 95  | A    |
| Tj                  | junction temperature                     |   | -   | -   | 125 | °C   |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{mb} \le 99$ °C; Fig. 1;<br>Fig. 2; Fig. 3                                 | -   | -   | 12  | А    |
| Static charact      | eristics                                 |   |     |     |     | ,    |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$        | -   | 5   | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$       | -   | 8   | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$<br>$T_j = 25 \text{ °C; } Fig. 7$ | -   | 10  | 35  | mA   |





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| Symbol              | Parameter                         | Conditions   |  | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|--|--|-----|-----|-----|------|
|                     |                                   | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$                         |  | -   | 22  | 70  | mA   |
| Dynamic chara       | Dynamic characteristics           |  |  |     |     |     | ,    |
| dV <sub>D</sub> /dt | rate of rise of off-state voltage | $V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit |  | 100 | 250 | -   | V/µs |

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                    | Simplified outline | Graphic symbol |
|-----|--------|--------------------------------|--------------------|----------------|
| 1   | T1     | main terminal 1                | mb                 | T2—T1          |
| 2   | T2     | main terminal 2                |                    | G<br>sym051    |
| 3   | G      | gate                           |                    | gv             |
| mb  | T2     | mounting base; main terminal 2 |                    |                |
|     |        |                                | TO-220AB (SOT78)   |                |

# 6. Ordering information

Table 3. Ordering information

| Type number  | Package  | kage   |         |  |  |  |
|--------------|----------|--|---------|--|--|--|
|              | Name     | Description  | Version |  |  |  |
| BT138-600    | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |
| BT138-600/DG | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max | Unit             |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | 600 | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$ ; Fig. 1;<br>Fig. 2; Fig. 3              | -   | 12  | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 | -   | 95  | А                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ;<br>$t_p = 16.7  \text{ms}$                 | -   | 105 | А                |
| I <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t <sub>p</sub> = 10 ms; sine-wave pulse   | -   | 45  | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T$ = 20 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs; T2+ G+                                 | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 20 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G-                           | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 20 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G-                           | -   | 50  | A/µs             |
|                     |                                      | $I_T$ = 20 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G+                           | -   | 10  | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 2   | Α                |
| P <sub>GM</sub>     | peak gate power                      |   | -   | 5   | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.5 | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40 | 150 | °C               |
| Tj                  | junction temperature                 |   | -   | 125 | °C               |

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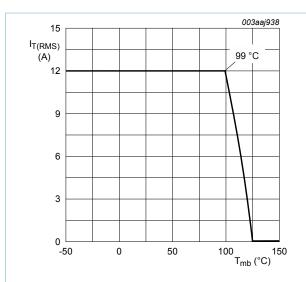
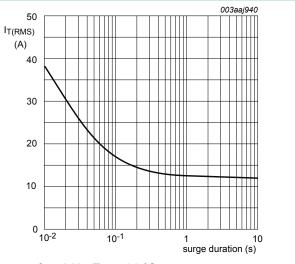
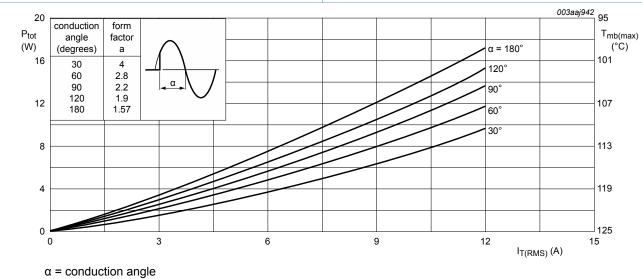


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz;  $T_{mb} = 99 \text{ }^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values



a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

Total power dissipation as a function of RMS on-state current; maximum values Fig. 3.

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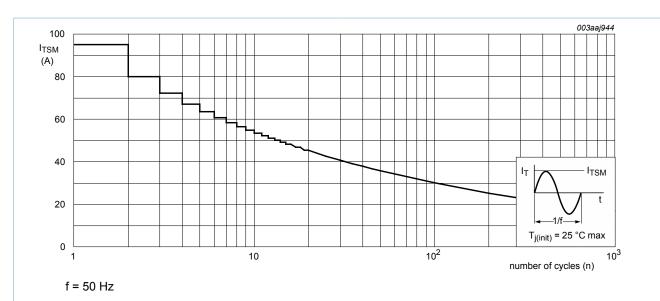
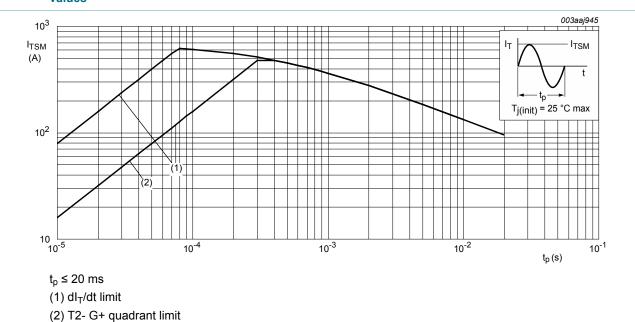


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter   | Conditions         | Min | Тур | Max | Unit |
|----------------------|---|--------------------|-----|-----|-----|------|
| uig iiib)            | thermal resistance<br>from junction to<br>mounting base | full cycle; Fig. 6 | -   | -   | 1.5 | K/W  |
|                      |   | half cycle; Fig. 6 | -   | -   | 2   | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance<br>from junction to<br>ambient       | in free air        | -   | 60  | -   | K/W  |

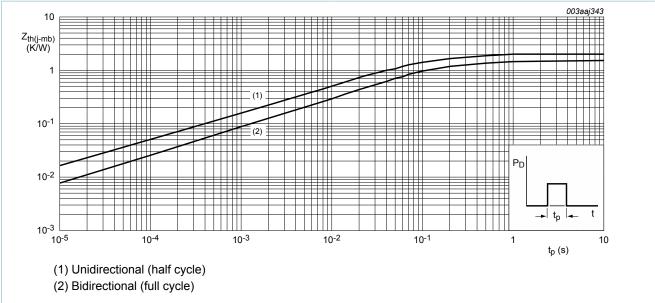


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

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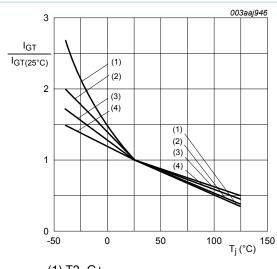
## 9. Characteristics

Table 6. Characteristics

| Symbol              | Parameter                         | Conditions   | Min      | Тур | Max  | Unit |
|---------------------|-----------------------------------|--|----------|-----|------|------|
| Static char         | racteristics                      |  | '        |     |      |      |
| I <sub>GT</sub>     | gate trigger current              | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$            | -        | 5   | 35   | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$ | -        | 8   | 35   | mA   |
|                     |                                   | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;}$<br>$T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$    | -        | 10  | 35   | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$            | -        | 22  | 70   | mA   |
| L                   | latching current                  | V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+;<br>T <sub>j</sub> = 25 °C; <u>Fig. 8</u>                      | -        | 7   | 40   | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$               | -        | 20  | 60   | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$ | -        | 8   | 40   | mA   |
|                     |                                   | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$            | -        | 10  | 60   | mA   |
| н                   | holding current                   | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>   | -        | 6   | 30   | mA   |
| / <sub>T</sub>      | on-state voltage                  | I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>  | -        | 1.4 | 1.65 | V    |
| V <sub>GT</sub>     | gate trigger voltage              | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11   | -        | 0.7 | 1    | V    |
|                     |                                   | V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C;<br>Fig. 11                                  | 0.25     | 0.4 | -    | V    |
| D                   | off-state current                 | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -        | 0.1 | 0.5  | mA   |
| Dynamic c           | haracteristics                    |  | <u> </u> | -   |      |      |
| dV <sub>D</sub> /dt | rate of rise of off-state voltage | $V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit           | 100      | 250 | -    | V/µs |
| t <sub>gt</sub>     | gate-controlled turn-on time      | $I_{TM}$ = 16 A; $V_D$ = 600 V; $I_G$ = 0.1 A; $dI_{G}/dt$ = 5 A/ $\mu$ s  | -        | 2   | -    | μs   |

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

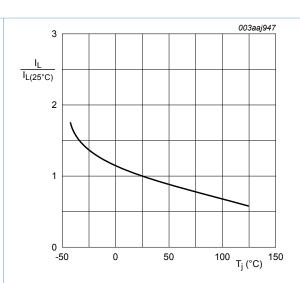
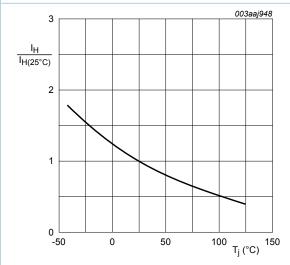
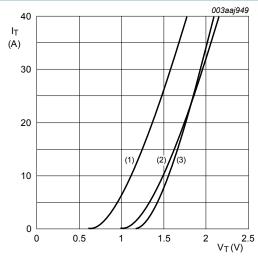


Fig. 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of junction temperature



 $V_o = 1.175 \text{ V}; R_s = 0.0316 \Omega$ 

- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>j</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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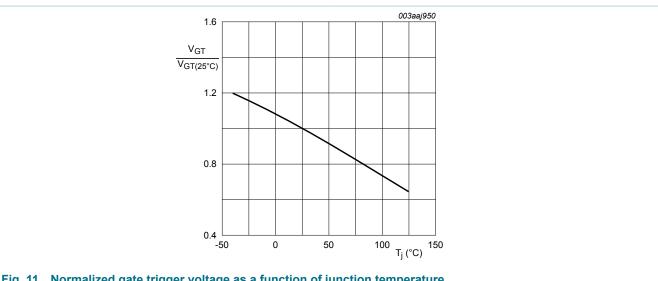
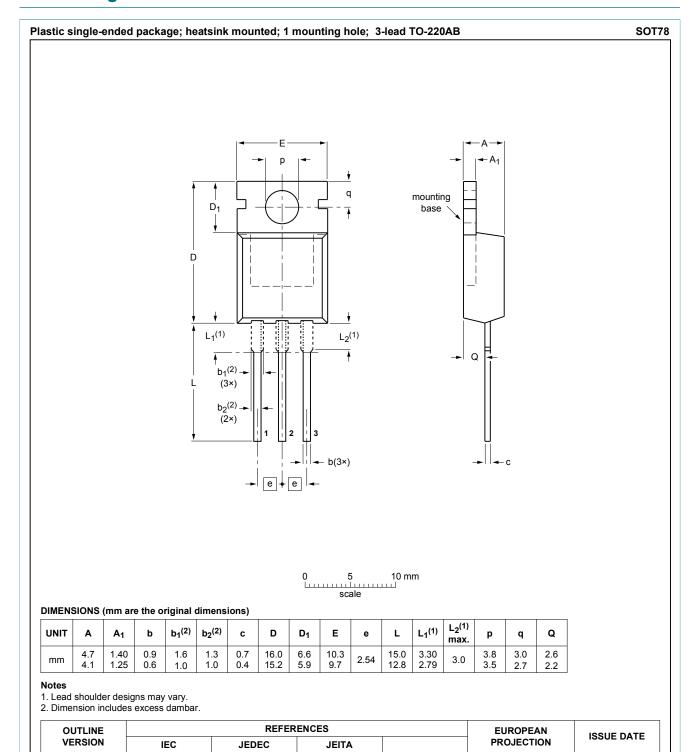


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

**4Q Triac** 

## 10. Package outline



# SOT78 3-lead TO-220AB

Fig. 12. Package outline TO-220AB (SOT78)

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### **4Q Triac**

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